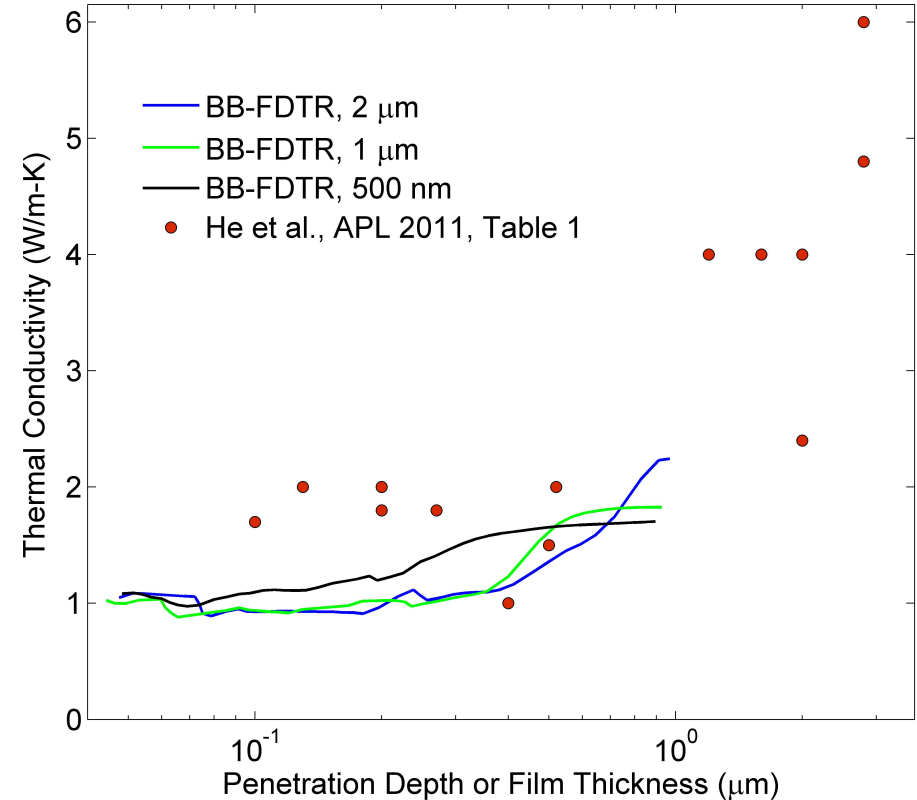
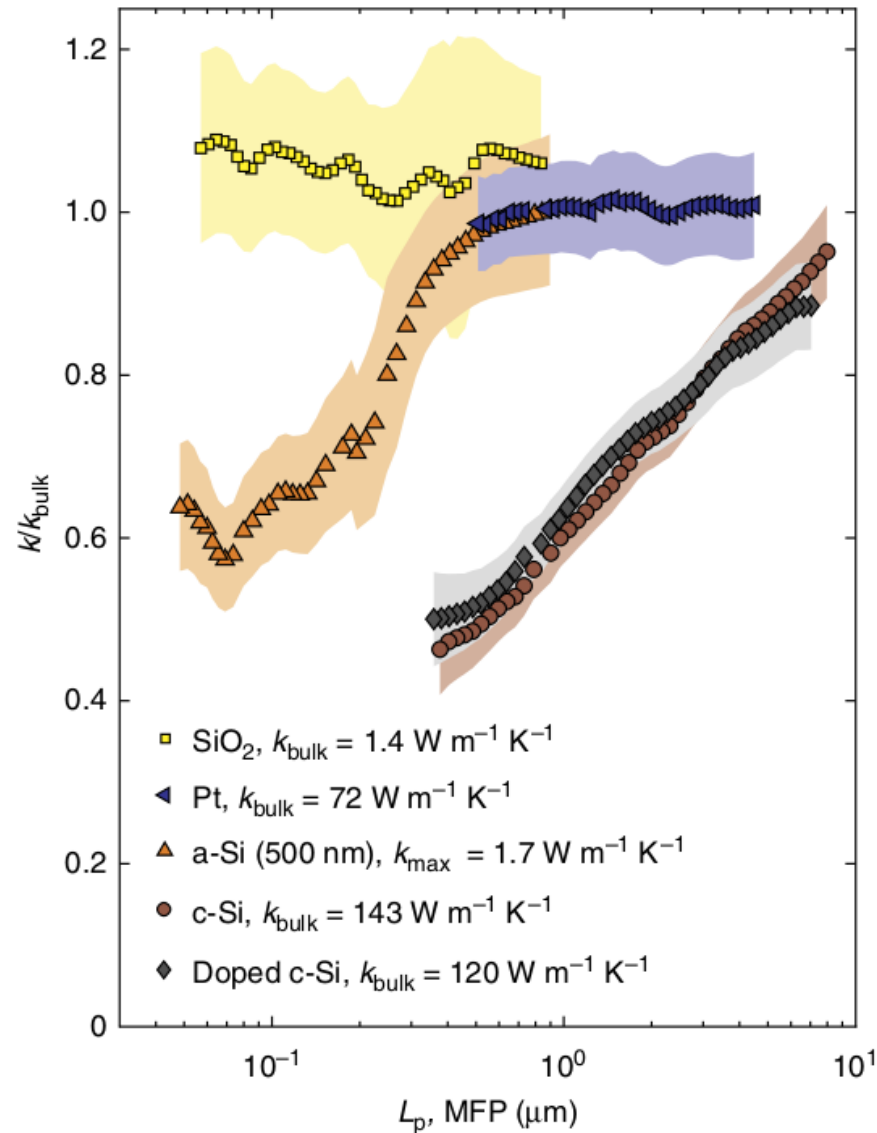


a-SiO₂, a-Si: broadband experiments

1



vibrational thermal conductivity

$$k_{vib} = k_{ph} + k_{AF}$$

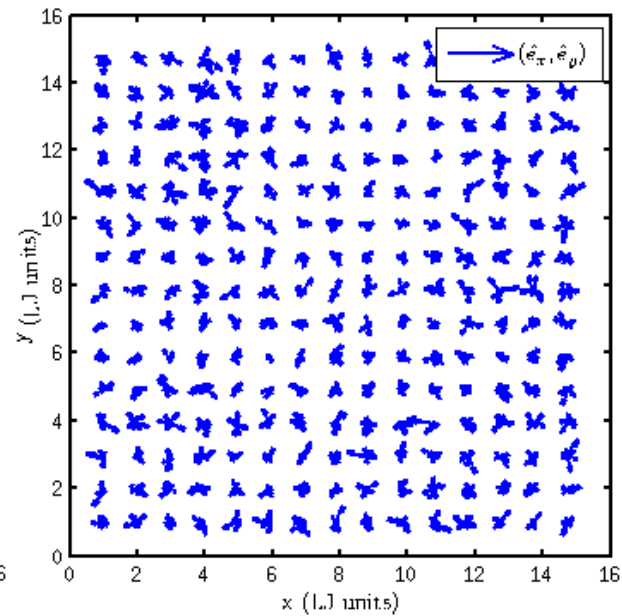
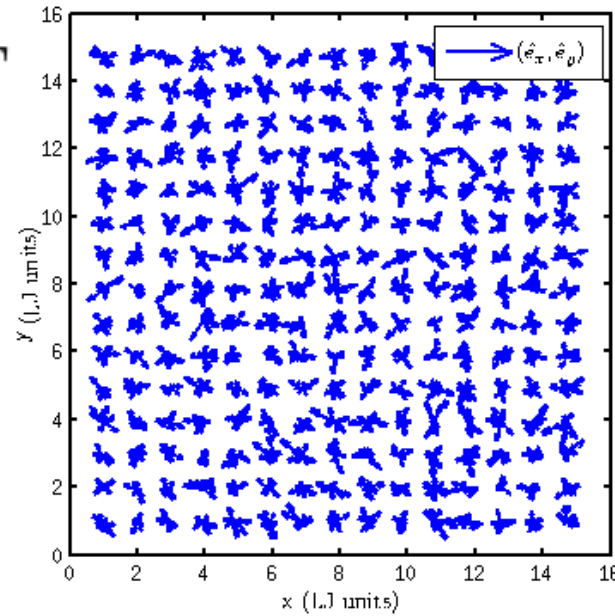
$$k_{ph} = \frac{1}{V} \int_0^{\omega_{cut}} d\omega DOS(\omega) C(\omega) D(\omega) \quad C(\omega) = k_B$$

$$D(\omega) = \frac{1}{3} v_g^2(\omega) \tau(\omega) \quad \Lambda(\omega) = v_g(\omega) \tau(\omega) \quad D(\omega) = \frac{1}{3} v_g(\omega) \Lambda(\omega)$$

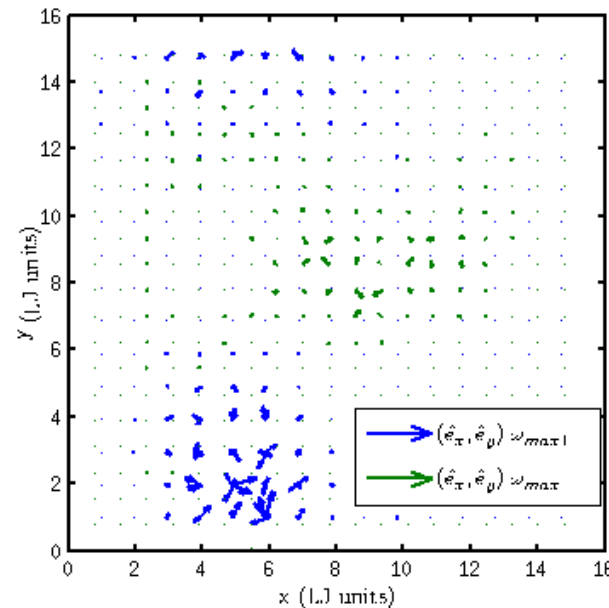


AF theory

$$k_{vib} = k_{ph} + k_{AF}$$

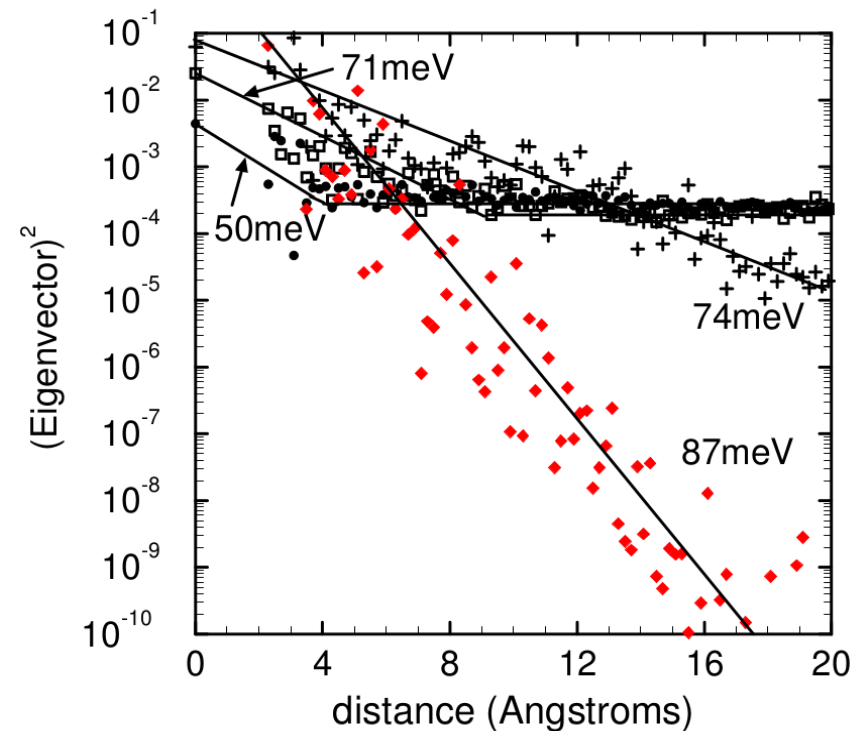
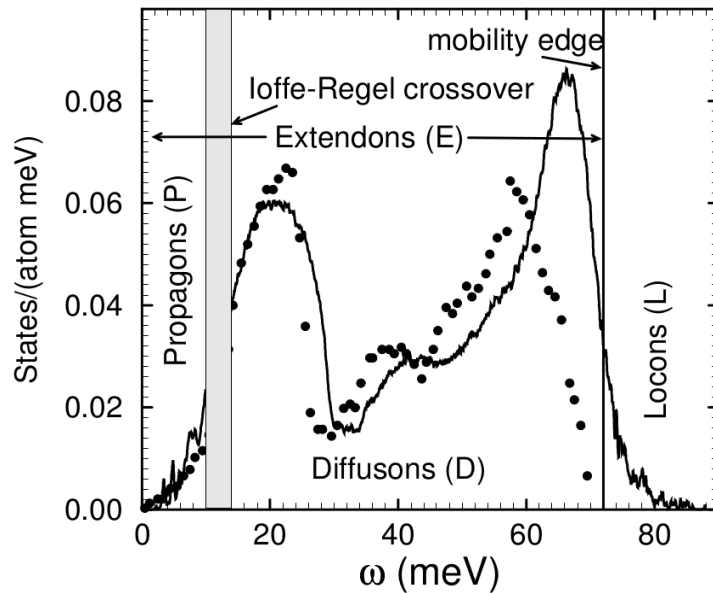


$$k_{AF} = \frac{1}{V} \sum_{\omega_i > \omega_{cut}} C_i(\omega) D_{AF,i}(\omega)$$



vibrons: propagons, diffusons, locons

vibrons $\left\{ \begin{array}{l} \text{extendons} \\ \text{locons} \end{array} \right\}$ $\left\{ \begin{array}{l} \text{propagons} \\ \text{diffusons} \end{array} \right\}$



thermal diffusivity limits

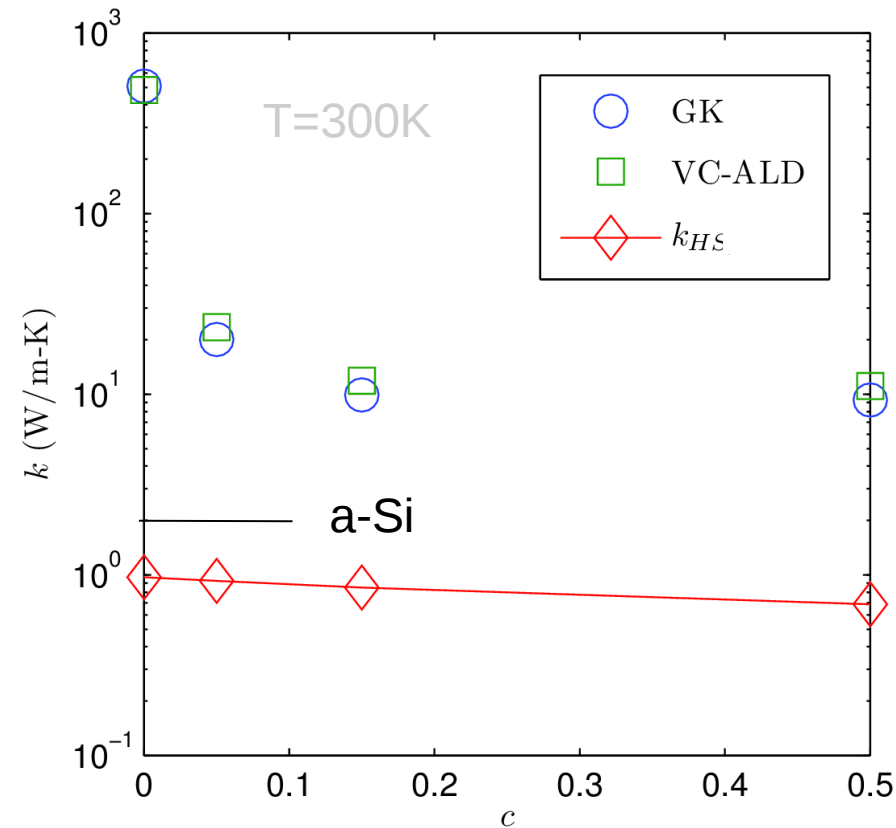
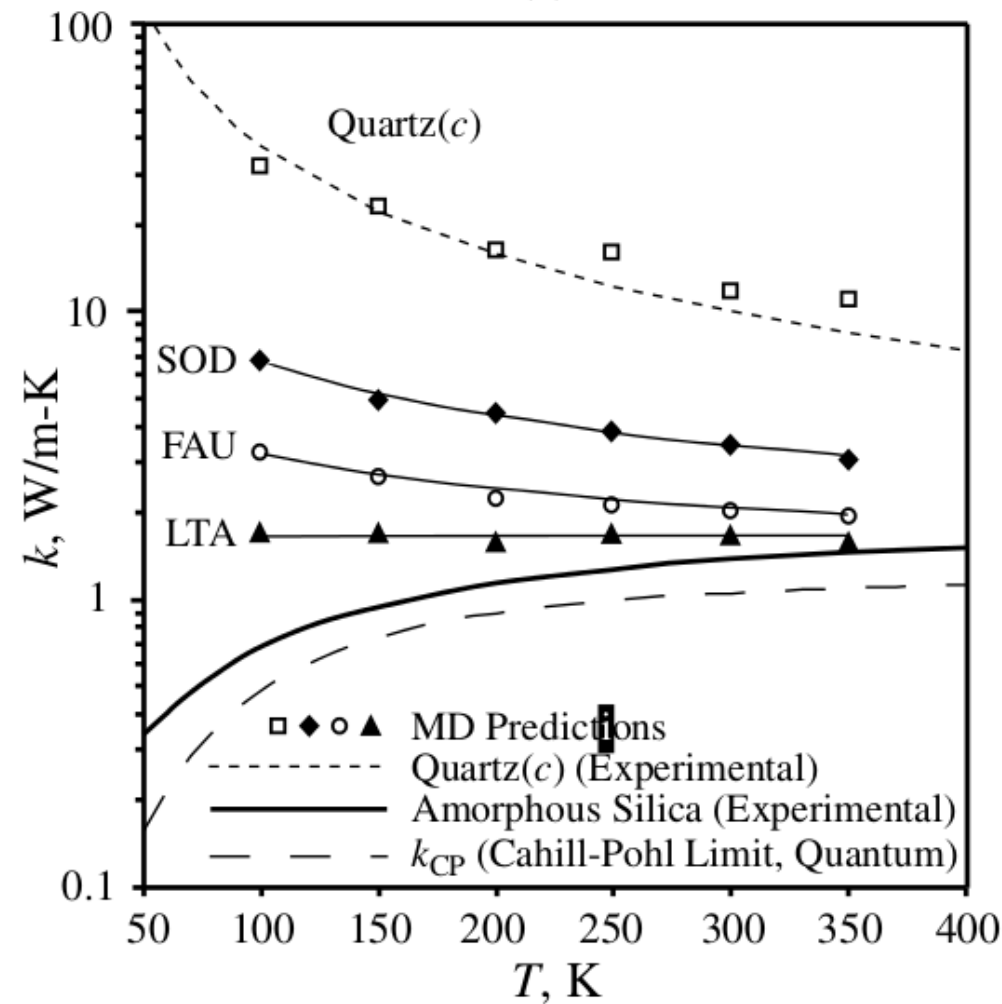
$$D(\omega) = \frac{1}{3}v_g^2(\omega)\tau(\omega) \begin{cases} \nearrow D(\omega) = B\omega^{-2} \\ \searrow D(\omega) = B\omega^{-4} \end{cases}$$

$$D_{HS} = \frac{1}{3}v_s a$$

$$k_{HS} = \frac{k_B}{V_b} b v_s a$$



silica, silicon thermal conductivity

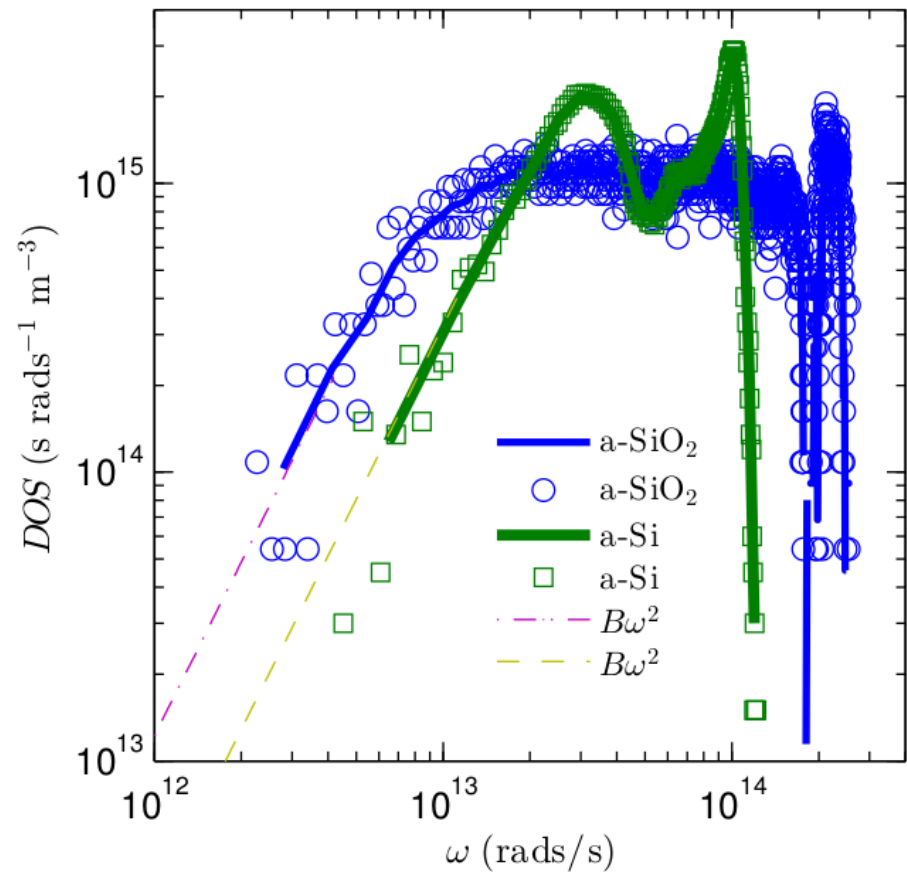


density of states

$$DOS(\omega) = \sum_i \delta(\omega_i - \omega)$$

$$DOS(\omega) = \frac{3\pi\omega^2}{2v_{s,DOS}^3}$$

$$v_s = \frac{2}{3}v_{s,L} + \frac{1}{3}v_{s,T}$$



method	Eqs. (17), (18)	Eqs. (20), (24)	DOS Eq. (10)
a-Si			
transverse	3,886	3,699	3,615
longitudinal	8,271	8,047	

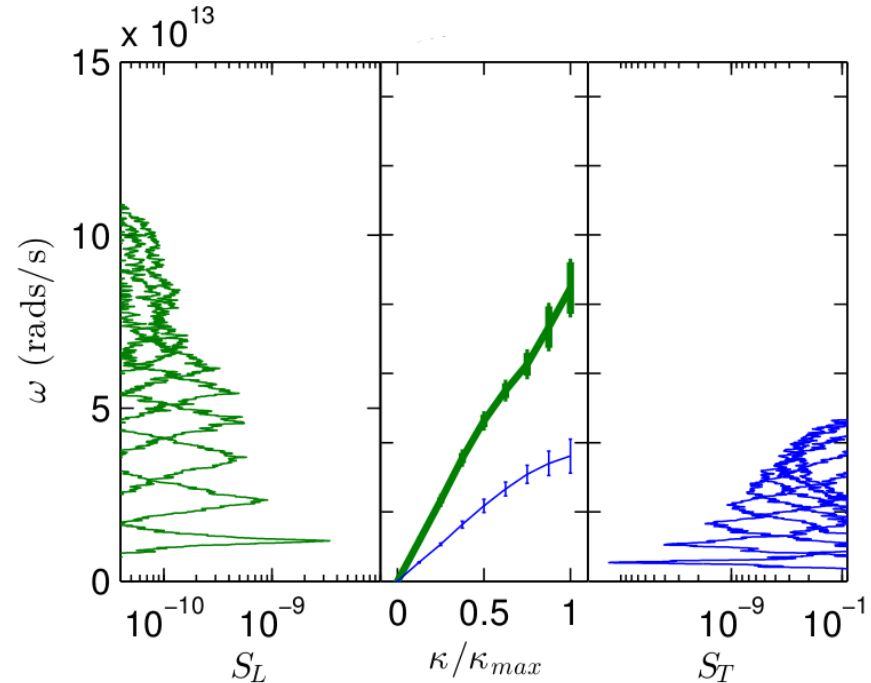
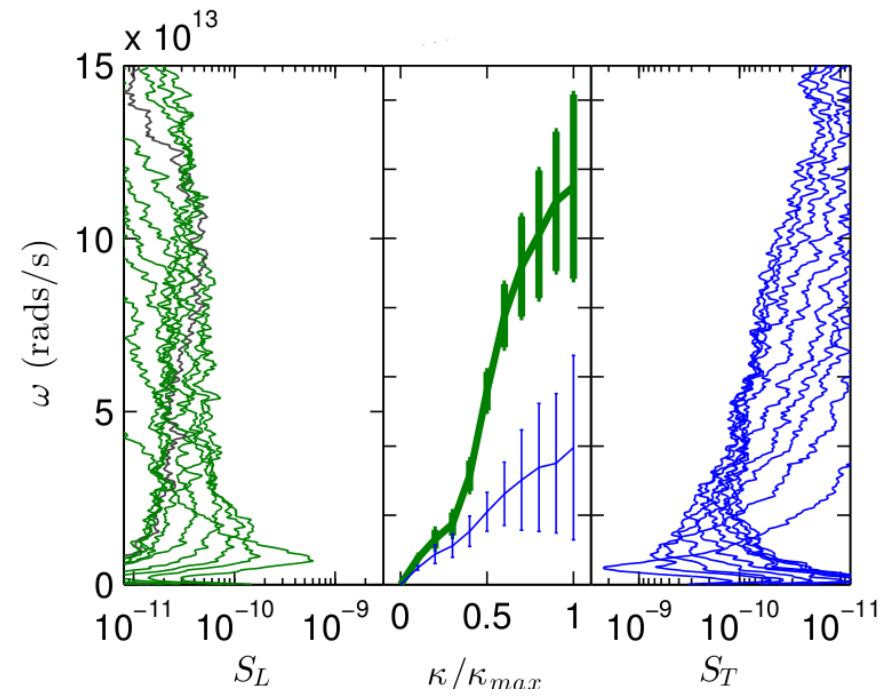
structure factor

$$E^L(\boldsymbol{\kappa}_\nu) = \left| \sum_b \hat{\boldsymbol{\kappa}} \cdot \mathbf{e}(\boldsymbol{\kappa}_\nu = \mathbf{0} \atop b \atop \alpha) \exp[i\boldsymbol{\kappa} \cdot \mathbf{r}_0(l=0 \atop b)] \right|^2$$

$$E^T(\boldsymbol{\kappa}_\nu) = \left| \sum_b \hat{\boldsymbol{\kappa}} \times \mathbf{e}(\boldsymbol{\kappa}_\nu = \mathbf{0} \atop b \atop \alpha) \exp[i\boldsymbol{\kappa} \cdot \mathbf{r}_0(l=0 \atop b)] \right|^2$$

$$S^{L,T}(\boldsymbol{\kappa}_\omega) = \sum_\nu E^{L,T}(\boldsymbol{\kappa}_\nu) \delta(\omega - \omega(\boldsymbol{\kappa}_\nu = \mathbf{0}))$$

$$S^{L,T}(\boldsymbol{\kappa}_\omega) = \frac{C_0(\boldsymbol{\kappa})}{[\omega_0(\boldsymbol{\kappa}) - \omega]^2 + \Gamma^2(\boldsymbol{\kappa})}$$



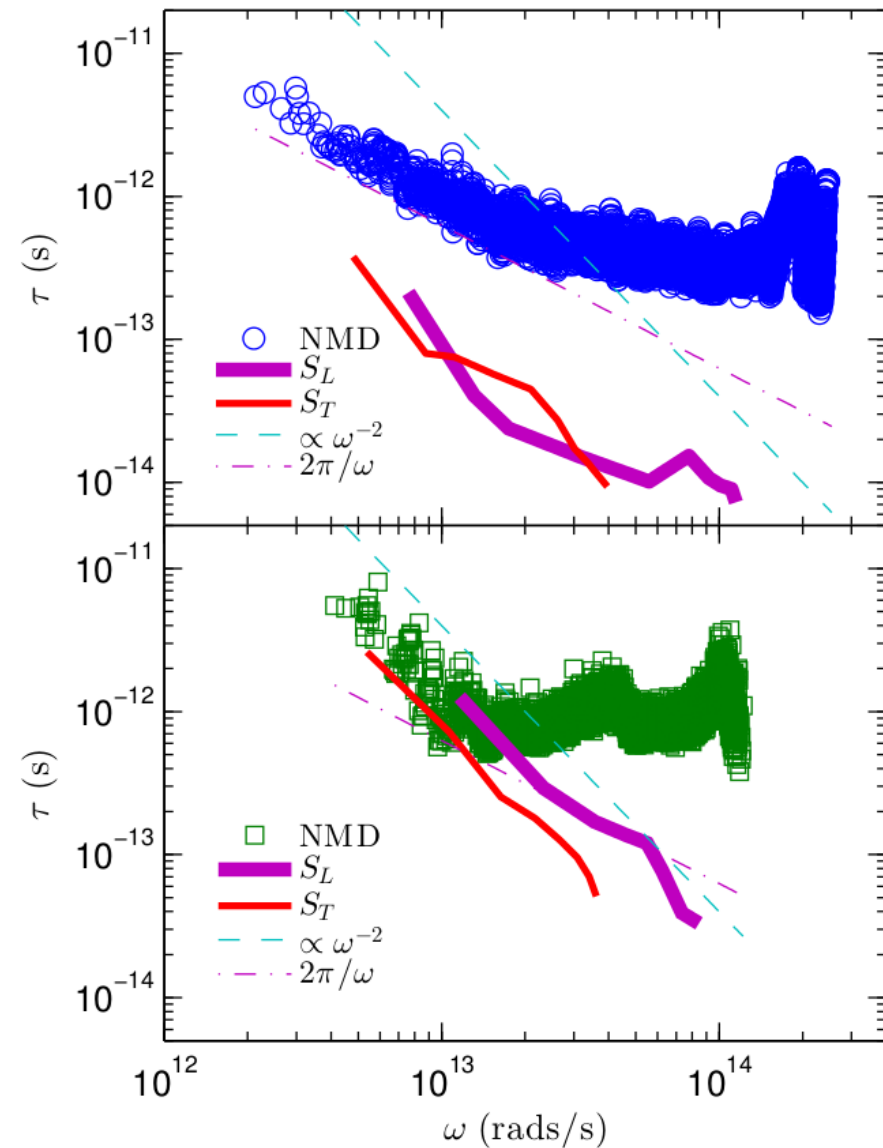
normal mode decomposition

$$\dot{q}(\boldsymbol{\kappa}=\mathbf{0}; t) = \sum_{\alpha, b, l}^{3, n, N} \sqrt{\frac{m_b}{N}} \dot{u}_{\alpha}(l; t) e^{*}(\boldsymbol{\kappa}=\mathbf{0} \quad b)_{\alpha} \exp[i(\mathbf{0} \cdot \mathbf{r}_0(l))]_{\alpha}$$

$$\Phi(\nu, \omega) = \lim_{\tau_0 \rightarrow \infty} \frac{1}{2\tau_0} \left| \frac{1}{\sqrt{2\pi}} \int_0^{\tau_0} \dot{q}(\boldsymbol{\kappa}=\mathbf{0}; t) \exp(-i\omega t) dt \right|^2$$

$$\Phi(\nu, \omega) = \frac{C_0(\nu)}{[\omega_0(\nu) - \omega]^2 + \Gamma^2(\nu)}$$

$$\tau(\nu) = \frac{1}{2\Gamma(\nu)}$$



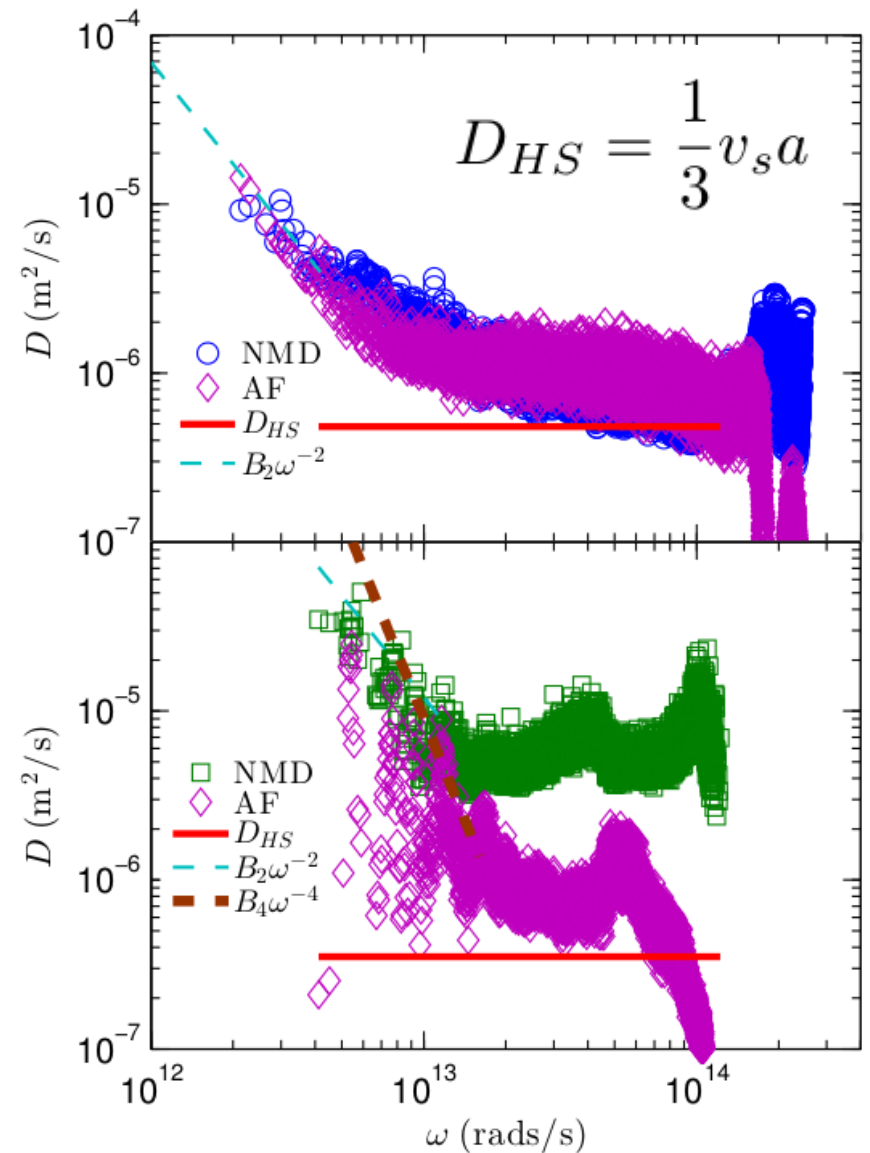
mode diffusivities

$$D(\omega) = \frac{1}{3} v_s \tau(\omega)$$

$$D_{AF,i} = \frac{\pi V^2}{\hbar^2 \omega_i^2} \sum_{j \neq i} |\langle i | J_{x,y,z} | j \rangle|^2 \delta(\omega_i - \omega_j)$$

$$D(\omega) = B\omega^{-2}$$

$$D(\omega) = B\omega^{-4}$$

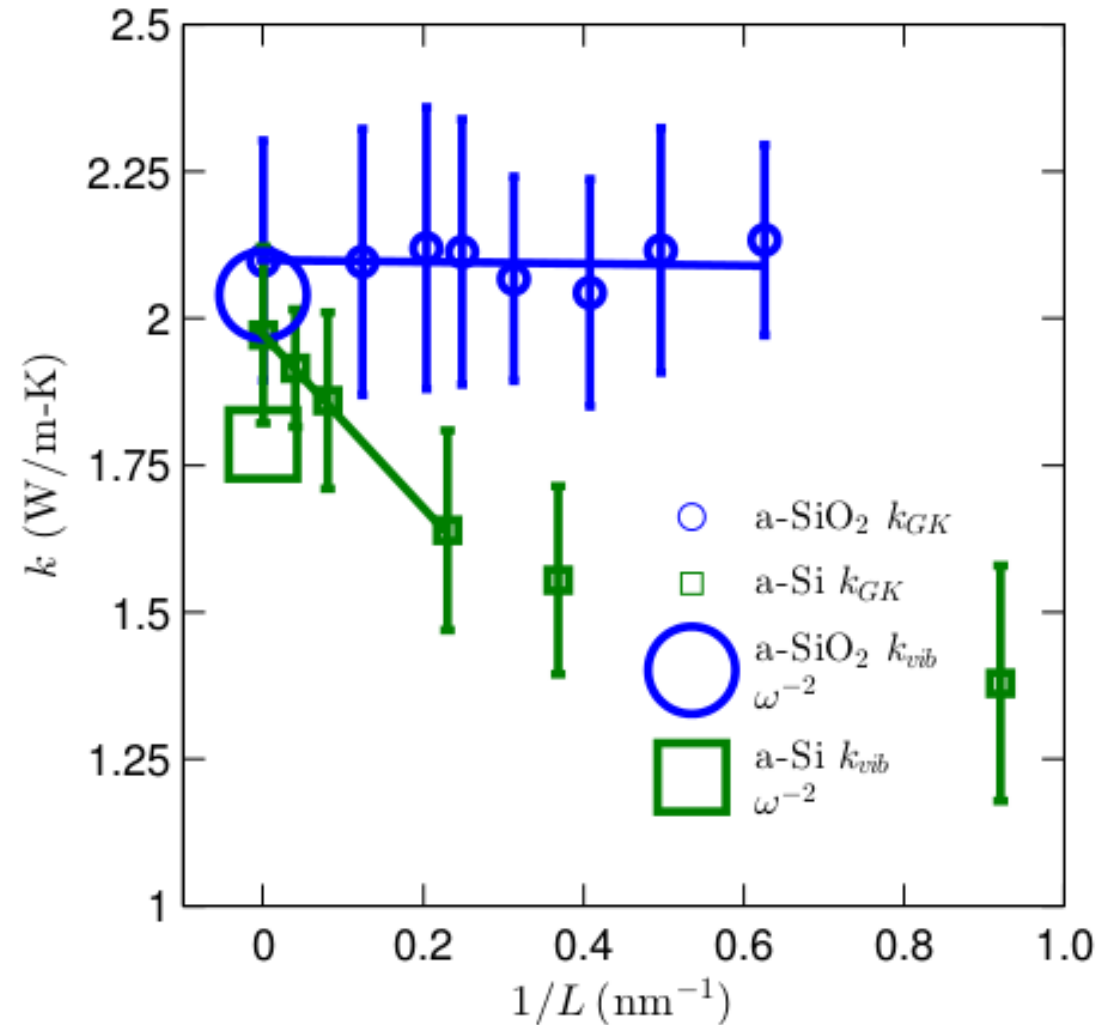


bulk thermal conductivity

$$k_{vib} = k_{ph} + k_{AF}$$

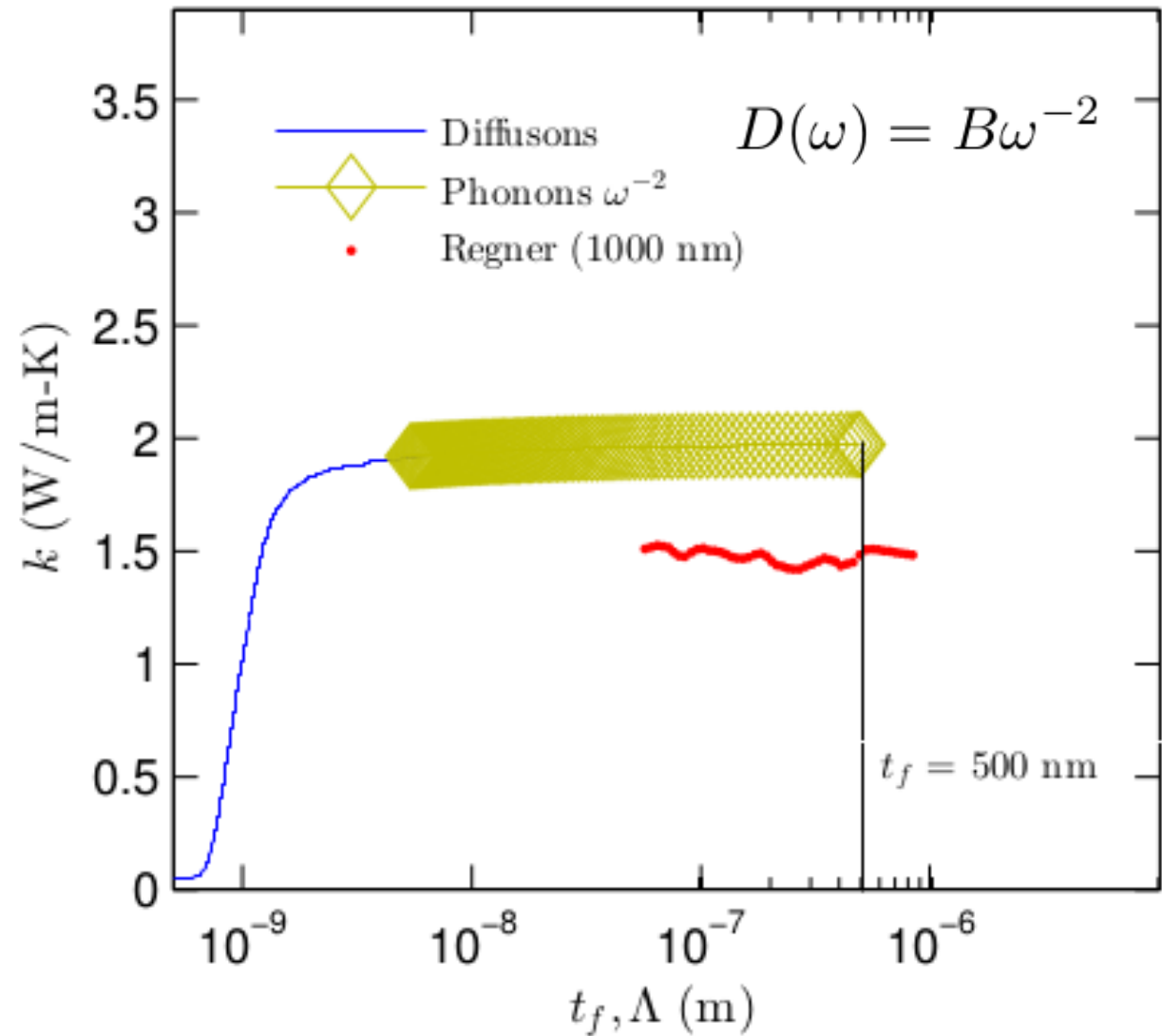
$$D(\omega) = B\omega^{-2}$$

$$\frac{k(L)}{k_{bulk}} = 1 - \frac{c_0}{L}$$



accumulated thermal conductivity: a-SiO₂

$$\frac{1}{\Lambda_{eff}(\omega)} = \frac{1}{\Lambda(\omega)} + \frac{1}{t_f}$$

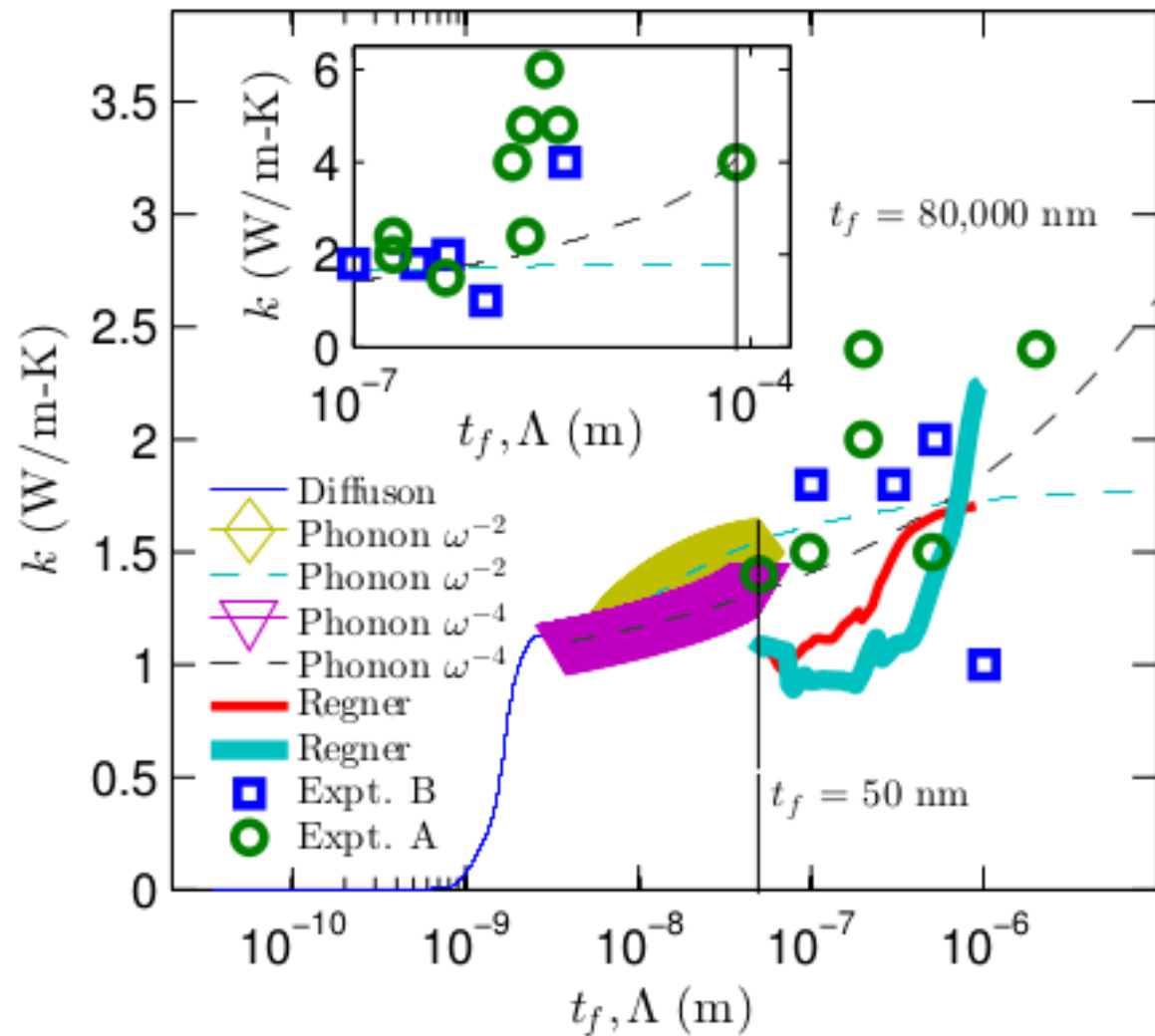


accumulated thermal conductivity: a-Si

$$\frac{1}{\Lambda_{eff}(\omega)} = \frac{1}{\Lambda(\omega)} + \frac{1}{t_f}$$

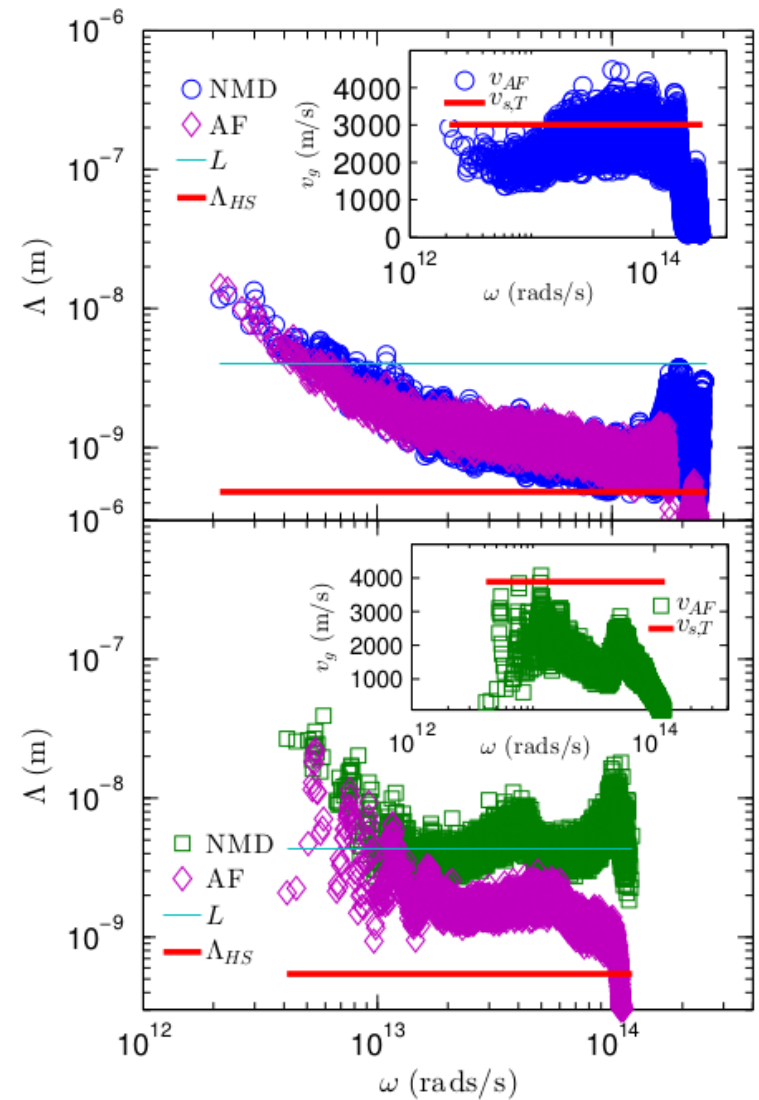
$$D(\omega) = B\omega^{-2}$$

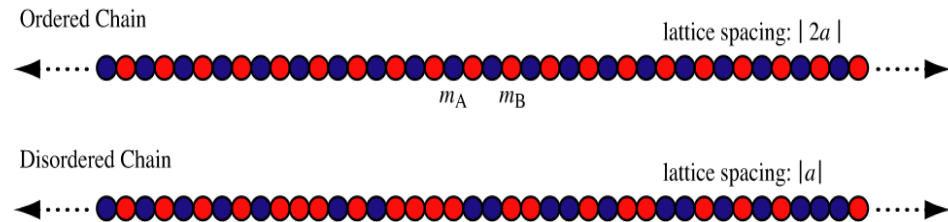
$$D(\omega) = B\omega^{-4}$$



$$v_{AF}(\omega) = \left(3 \frac{D_{AF,i}(\omega)}{\tau(\omega)} \right)^{1/2}$$

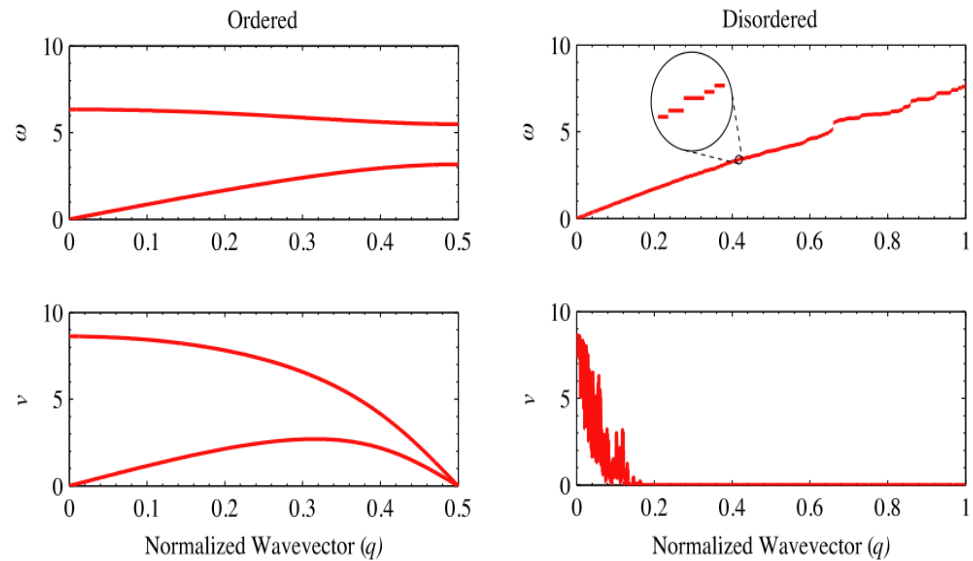
$$\Lambda_{AF}(\omega) = (3D_{AF,i}(\omega)\tau(\omega))^{1/2}$$





v_g from “zone-folding”:

<http://iopscience.iop.org/0953-8984/23/20/205401>



v_g from near [000]:

<http://pubs.acs.org/doi/abs/10.1021/nn2003184>

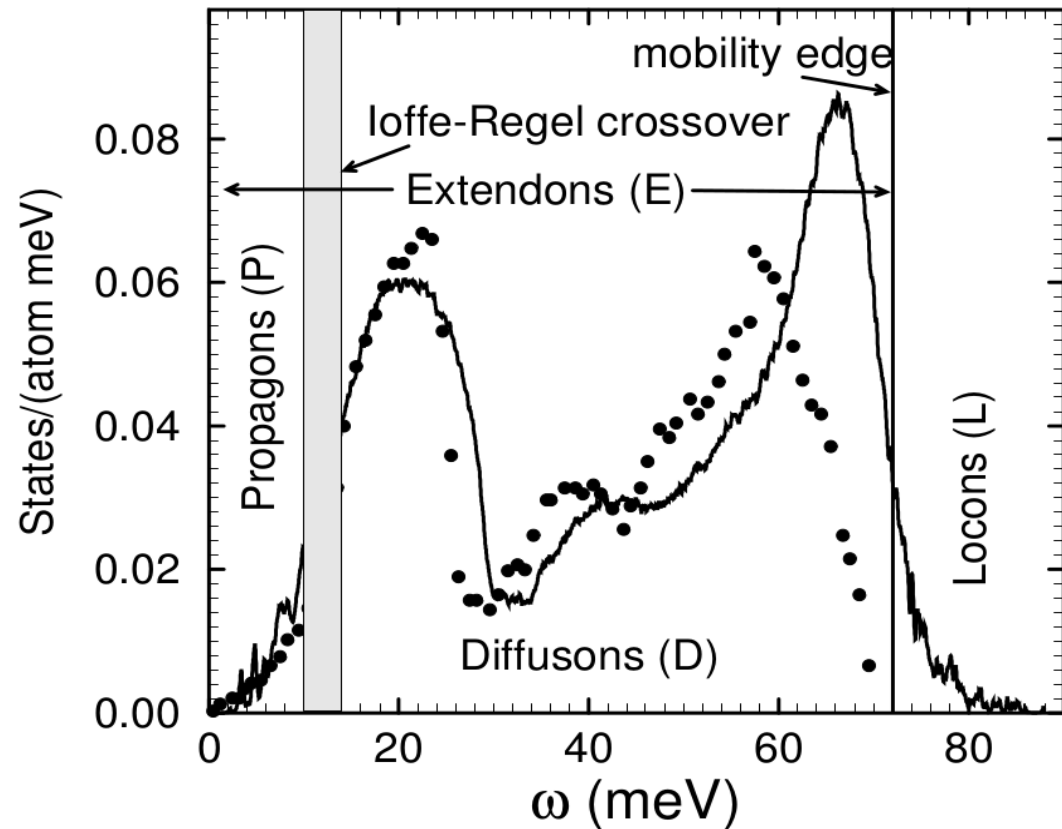
<http://pubs.acs.org/doi/abs/10.1021/nl201359q>

vibrons: propagons, diffusons, locons

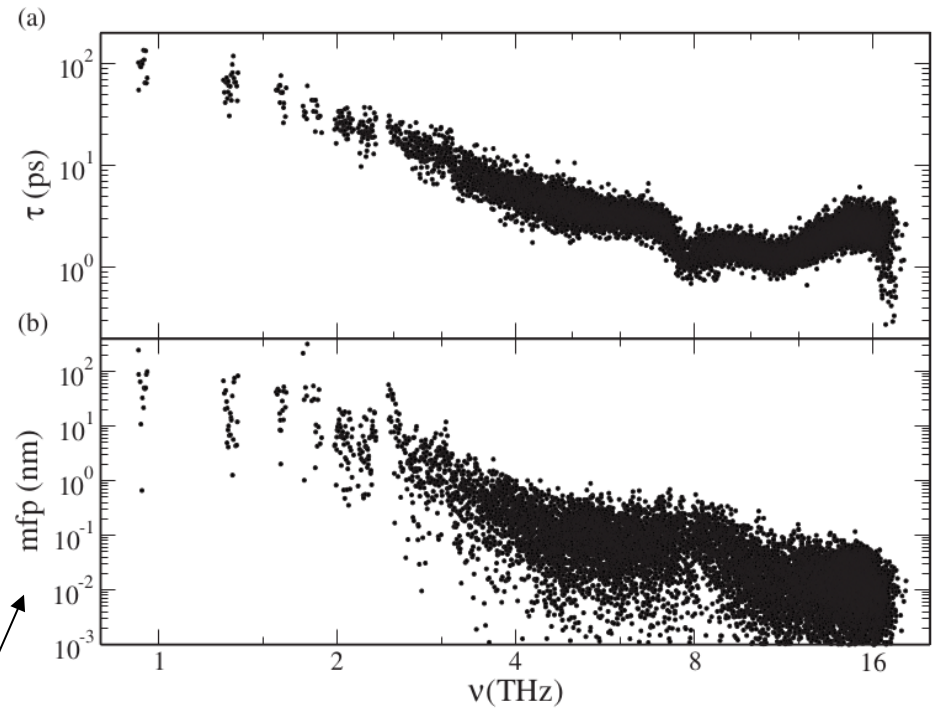
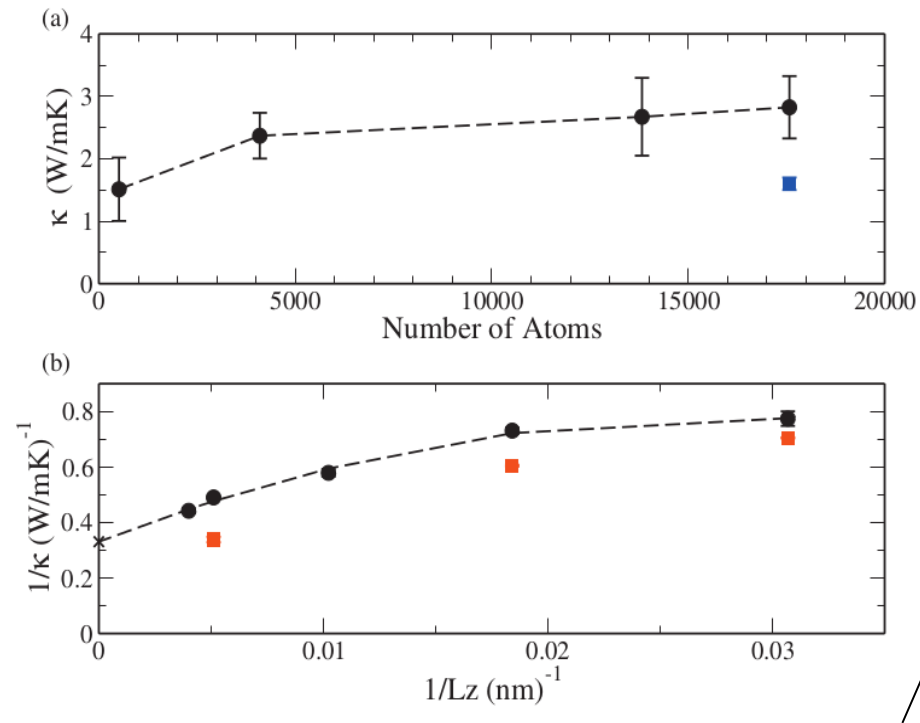
Numerical studies of amorphous silicon show that the lowest 4% of vibrational modes are plane-wave like (“propagons”) and the highest 3% of modes are localized (“locons”). The rest are neither plane-wave like nor localized. We call them “diffusons.”

\cite{diffusons_allen_1999}

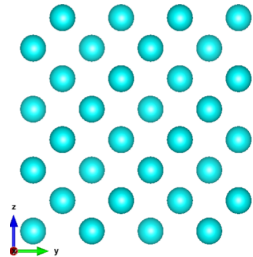
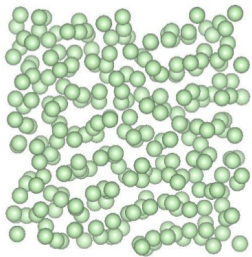
vibrons {
 extendons {
 propagons
 diffusons
 locons



A-Si: Tersoff



MD-based: size of simulation cell=4.3 nm



Appl. Phys. Lett. 98, 144101 (2011)

http://apl.aip.org/resource/1/applab/v98/i14/p144101_s1

